What is claimed is:

1. A method of fabricating a semiconductor device, comprising the step of:

forming a source and a drain doped with a first conductivity type in an active area on both sides of each word line by an isolation layer of a second conductivity type doped substrate, wherein each word line is separated by a predetermined interval;

forming a first contact and a second contact by using isolation layers which are separated by an interval which is wider in the source than in the drain to expose the source and the drain; and

selectively implanting a second conductivity type dopant ion in the source by using the isolation layer and each word line as an ion implanting mask during a tilt ion implantation process.

2. The method as recited in claim 1, wherein the tilt ion implantation process is carried out using a tilt angle of about 20° to about 25°.

3. The method as recited in claim 2, wherein the tilt ion implantation process is carried out using a twist of about 7° to about 18°.

4. The method as recited in claim 3, wherein the tilt

ion implantation process is carried out in a direction perpendicular to the word line.

5. The method as recited in claim 1, wherein the first conductivity type is N-type and the second conductivity type is P-type.

6. The method of fabricating the semiconductor device as recited in claim 5, wherein the second conductivity type dopant ion is a Boron.